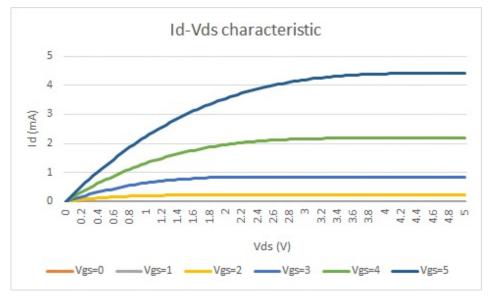


$$(ox = \frac{\xi_{ox}}{\xi_{ox}}$$

$$i_{m} \log \frac{W}{L} = 24 (.6_{M} [A/V^{2}]$$



$$I_{DSI} = \frac{1}{2} M_{\text{N}} C_{\text{OX}} \frac{W}{2L} \left(2(V_{\text{ND}} - V_{\text{C}}) V_{\text{DS}} - V_{\text{DS}}^{2} \right)$$

Vos-Vi < Vos, Vi < Vos, so both NMOS in (b) are in triode rigion.

$$I_{1052} = \frac{1}{2} \text{Marcox} \frac{W}{L} \left(2(V_{100} - V_t - V_t) (V_{05} - V_t) - (V_{105} - V_t)^2 \right) = 2kU_{05} + 2V_1^2 - 2(V_{05} + k)V_t$$

$$= \frac{1}{2} \text{Marcox} \frac{W}{L} \left(2(V_{00} - V_t) V_1 - V_t^2 \right) / e \in V_{00} - V_t = k.$$

 $2(|kV_{03}+V_{1}^{2}-(V_{03}+k_{0})V_{1})-V_{03}^{2}+2V_{03}V_{1}-2|kV_{1}=0)$ $2|V_{1}^{2}-4|k|V_{1}+2|kV_{03}-V_{03}|^{2}=0$

$$|V_{1}|^{2} = \frac{2k - \sqrt{4k^{2} + 2V_{DJ}^{2} - 4kV_{DJ}}}{2} = k - \sqrt{\frac{V_{DS}^{2} - kV_{DS} - k^{2}}{2}} = \frac{1}{2} M_{N}(ox \frac{W}{L}) = \frac{1}{2} M_{N}(ox \frac{W}{L}) = \frac{1}{2} M_{N}(ox \frac{W}{L}) = \frac{1}{2} M_{N}(ox \frac{W}{L}) = \frac{1}{2} M_{N}(ox \frac{W}{2L}) =$$

From 2.2, V, >0, Vsb >0. Then the depletion region of channel of top TR become wider, so Uth increase. It causes the Insz < Insi

$$C_{0x} = \frac{E_{0x}}{E_{0x}} = \frac{3.9 \times 8.85 \times (0^{-12} \times 90 \times 10^{-15})}{(6 \times 10^{-4} \times 90 \times 10^{-15})} = 1.94 \text{ f} = 1.9$$

2.5)

perimeter = 2W+2L = 187 = 5.4 mm (? process over than 0.35m)

$$(db = 1.8 \times 0.42f + 5.4 \times 0.33f = 1.538f$$

$$Cdb = 1.8 \times 0.925 \times (1 + \frac{5}{0.97}) + 5.4 \times 0.335 \left(1 + \frac{5}{0.97}\right)^{-0.12}$$

$$= 1.775 + F$$

Additiona)

$$V(x) = V_{6} - V_{t} - \sqrt{(V_{6} - V_{t})^{2} - \frac{2Z_{b}}{M_{b}C_{6x}W}} = V_{6} - V_{t} - \sqrt{(V_{6} - V_{t})^{2} - \frac{2(V_{6} - V_{t})V_{b} - \frac{1}{2}V_{b}^{2}}}$$

$$= 1.4 - \sqrt{1.96 - \frac{109}{9D}(2.8V_{D} - V_{D}^{2})2L}$$

